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Inclosure Material:
Metal all transistor
Overall Length:
1.573 inches all transistor
Overall Height:
0.350 inches
Overall Width:
1.050 inches all transistor
Mounting Facility Quantity:
2 all transistor
Internal Configuration:
Junction contact all transistor
Joint Electronic Device Engineering Council/jedec/case Outline Designation:
To-3 all transistor
Electrode Internally-electrically Connected To Case:
Collector all transistor
Internal Junction Configuration:
Npn all transistor
Component Function Relationship:
Matched
Component Name And Quantity:
2 transistor
Mounting Method:
Unthreaded hole all transistor
Features Provided:
Hermetically sealed case
Semiconductor Material:
Silicon all transistor
Voltage Rating In Volts Per Characteristic:
140.0 breakdown voltage, collector-to-emitter, base open all transistor
Current Rating Per Characteristic:
16.00 amperes source cutoff current all transistor
Power Rating Per Characteristic:
150.0 watts small-signal input power, common-collector absolute all transistor
Maximum Operating Tempurature Per Measurement Point:
175.0 degrees celsius junction all transistor
Terminal Type And Quantity:
2 pin all transistor and 1 case all transistor
Shelf Life:
N/a
Unit Of Measure:

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Demilitarization:

No

Fiig:

A110a0

